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G. Subramania, S. Foteinopoulou, and I. Brener Phys. Rev. Lett. **107**, 163902 — Published 13 October 2011 DOI: 10.1103/PhysRevLett.107.163902

## Non-resonant broadband funneling of light via ultra-subwavelength channels

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## Abstract

Enhancing and funneling light efficiently through deep sub-wavelength apertures is essential in harnessing light-matter interaction. Thus far, this has been accomplished resonantly, by exciting the structural surface plasmons of perforated nanostructured metal films, a phenomenon known as extra-ordinary optical transmission (EOT). Here, we present a new paradigm structure which possesses all the capabilities of EOT platforms, yet operates non-resonantly on a distinctly different mechanism. Our proposed platform demonstrates efficient ultra-broadband funneling of optical power confined in an area as small as  $\sim (\frac{\lambda}{500})^2$ , where optical fields are enhanced, thus exhibiting functional possibilities beyond resonant platforms. We analyze the non-resonant mechanism underpinning such phenomenon with a simple quasi-static picture, which shows excellent agreement with our numerical simulations.

PACS numbers: 42.25.-p, 78.67.-n, 41.20.Jb, 78.20.Ci

Confining and enhancing light within deep subwavelength volumes is key to the enhancement of light-matter interaction with great implications in the control of absorption and emission rates, as well as in attaining high optical nonlinearities and/or gain. However, certain applications also crucially require efficient power funneling of the confined and enhanced electromagnetic (EM) fields. Such phenomenon was demonstrated for the first time in a thin silver film patterned with subwavelength sized cylindrical holes<sup>1</sup>. In that work, the transmitted light is beyond the expectations of Bethe's theory<sup>2,3</sup> and twice the amount predicted from a simple analysis based on the area fraction of the holes. Therefore such phenomenon was termed as Extra-ordinary Optical Transmission (EOT). An important goal has been towards optimization of the pertinent features of the phenomenon<sup>4</sup>: field confinement and enhancement, and power throughput exceeding the area fraction of the holes. Both possible proposed mechanisms underpinning the EOT phenomenon -surface plasmon excitation<sup>5</sup> and dynamic diffraction<sup>6</sup>- consent that it is a resonant phenomenon.

Resonant phenomena have unavoidably a narrow spectral bandwidth. There can be some rather limited control of the bandwidth by engineering the interaction between resonances. For example, by exploiting coupled resonances, a broadened bandwidth was observed in the enhancement around nanoparticle dimers<sup>7</sup> or in the transmission through a metallic grating<sup>8</sup>. Typically, this type of approach would require fine tuning of the structural features, – size<sup>7,8</sup>, shape<sup>9–12</sup> and/or angle of wave incidence<sup>8</sup>. It is therefore of utmost interest to explore the possibility to access the attractive features of the EOT phenomenon, pertinent to practical applications, but without invoking any resonances. Very recently, Alu et al.<sup>13</sup> reported a non-resonant approach to a broadband transmission of P-polarized light through a metallic grating structure, occuring at the Brewster angle of the corresponding effective medium. Nevertheless, such platform does not offer a two-dimensional confinement of the optical fields and leads to poor field enhancement due to the reduced tangential electric field component<sup>13</sup>. Moreover, the required oblique incidence at large angles can be considerably less practical.

In this Letter, we explore highly-efficient funneling of light enhanced in intensity through deep sub-wavelength apertures facilitated by means of a non-resonant mechanism. We propose a paradigm structure which comprises of periodic connected rectangular apertures of two different sizes operating under normal incidence. The larger aperture aids the coupling of the incoming light while a significant fraction of the incident power is funneled through the smaller aperture. The non-resonant operation renders the proposed structure functional in a very broad wavelength range, starting from 3 microns and continuing well into far-IR wavelengths. The mid-IR wavelength range is of particular interest for molecular fingerprinting/sensing<sup>14</sup> as well as detectors<sup>15</sup>. The broadband functionality allows for flexible utilization in many applications thus considerably relaxing strigent design requirements of resonant devices. We will demonstrate in the following how our proposed structure functions as a broadband non-resonant platform that funnels power through a region as small as  $(\sim \lambda/500)^2$  [at 20 micron wavelength] accompanied by highly enhanced EM fields.

The proposed structure is a square lattice of period a, consisting of alternating small and large rectangular slits engraved on a thin Au film of thickness  $d_{Au}$  resting on top a substrate of refractive index of n = 1.45 and thickness  $d_{sub}$  (Fig. 1). The dimensions of the large and small slits are shown in the right panel of Fig. 1. In the limit of  $w_{x1} = 0$  we obtain a rectangular hole structure. When  $w_{x1}=w_{x2}$  we obtain a wire-grid (WG) structure, which is widely used as a polarizer due to the polarization selective broadband transparency properties<sup>16</sup>. In the following we will refer to our proposed structure, where neither  $w_{x1}=w_{x2}$ , nor  $w_{x1} = 0$ , as the double-groove (DG) structure.

To understand and explore the optical capabilities of the DG structure we study numerically the corresponding transmission spectrum between the wavelength range of 3 - 20 microns. We employ the Finite Difference Time Domain (FDTD) approach<sup>17</sup>, alongside with the Auxiliary Differential Equation (ADE)<sup>7,17</sup> method suitable for the modeling of the Drude dispersion<sup>18</sup> for the permittivity [ $\varepsilon(\omega)$ ] in time domain<sup>7</sup>. For comparison, we consider five different structures (two DG two WG structures and one rectangular-hole structure). All are chosen to be deeply subwavelength to target the widest operation wavelength regime in the mid-IR while being realistically achievable with nanofabrication methods<sup>19</sup>.

We show the simulation results for the transmission in Fig. 2 versus the free space wavelength,  $\lambda_{\rm free}$ , for a plane wave impinging the structure normally along the z-direction, with electric field polarized along the x-direction. All the considered structures have the following feature-size parameters common: a=300 nm, d<sub>Au</sub> = 50nm, d<sub>sub</sub>= 500nm, and  $w_y = 200$  nm. We observe very low transmission for the rectangular structure ( $w_{x1} =$ 0 nm and  $w_{x2} = 100$  nm), represented with the dot-dashed line in the figure. This is expected for a structure comprising of closed shaped apertures, for wavelengths above the EOT resonance<sup>2,3</sup>. On the other hand, all structures with unbounded apertures are highly transmissive. In particular, both DG structures –with ( $w_{x1}, w_{x2}$ ) = (15nm, 100nm), and  $(w_{x1}, w_{x2}) = (50 \text{nm}, 100 \text{nm})$  respectively– remain highly transmissive throughout the 3 – 20 microns range. The corresponding transmission (solid and dashed lines in the figure) lies between that of the 100 nm WG (dotted line) and the 15 nm WG (long-dashed line). The transmission drops sharply around ~ 3 microns when the incoming fields start to sense the spatial periodicity of the structures<sup>20</sup>. Interestingly, the reduction in total transmission, in reference to the 100 nm WG transmission, is disproportionate with respect to the reduction in  $w_{x1}$ , with  $w_{x1} = 50$  nm showing negligible change, and  $w_{x1} = 15$  nm showing a maximum reduction of ~ 20%.

To understand this behavior we calculate the spatial distributions<sup>21</sup> (Fig. 3) of the modal electric field (magnitude of x-component) normalized to the incident electric field at a wavelength of 10 microns, for the cases depicted in Fig. 2. We observe small field values for the rectangular hole structure (not in figure). For the DG structures [Figs. 3 (a) and (b)] we observe a highly enhanced field in the small-gap region –which is higher the narrower the small-gap slit– and a small field in the large-gap region. Also, the electric fields remains nearly uniform in the small- and large-slit regions, except for a small fringing at the sharp interface between the two slits. The two WG structures, representing the extreme cases for Fig. 3(a) and (b) with  $w_{x2} \rightarrow w_{x1} = 15$  nm and  $w_{x1} \rightarrow w_{x2} = 100$  nm respectively, show lower field enhancement values. Strikingly, for both the DG structures, a closer examination of the the ratio of the x-component of the electric field in the middle of the small and large slit, reveals it to be very close to the ratio  $w_{x2}/w_{x1}$ .

Therefore, we further examine this ratio throughout the spectrum of interest (3-20 microns) for the DG structures of Figs. 3(a) and 3(b) and show our results in Fig. 4(a). We observe that indeed, within this wavelength regime,  $E_S/E_L \approx w_{x2}/w_{x1}$ , with  $E_S$  and  $E_L$  being the electric field amplitude in the center of the small and large slit, respectively. This can be explained with a simple quasi-static picture wherein the electrons in the metal respond nearly instantaneously to the incident field. The charges build up across the gaps as depicted in the schematics (right panel of Fig. 4). As a result, the potential difference across the small slit, [points (1) and (2)] is equal to the potential difference across the large slit [points (3) and (4)]. This implies uniform electric field in each respective slit region with no phase difference and an amplitude ratio equal to the inverse of the ratio of the respective widths, as we have observed. In the long-wavelength regime, we can assume the structures are nearly transparent (i.e. almost zero reflection). We apply the continuity

of the tangential component of the electric field at the interface<sup>23</sup>, but averaged over the structural unit cell,and obtain:

$$\frac{\mathrm{E}_{\mathrm{L}}\mathrm{w}_{\mathrm{x2}}\mathrm{w}_{\mathrm{y}} + \mathrm{E}_{\mathrm{S}}\mathrm{w}_{\mathrm{x1}}(\mathrm{a} - \mathrm{w}_{\mathrm{y}})}{a^{2}} \cong \mathrm{E}_{0},\tag{1}$$

with  $E_0$  being the source amplitude. Using in conjunction the quasistatic condition for the  $E_S/E_L$  ratio we get:

$$\frac{E_L}{E_0} \approx \frac{a}{w_{x2}}$$
, 2(a) and  $\frac{E_S}{E_0} \approx \frac{a}{w_{x1}}$  2(b)

We notice that this simple long-wavelength picture predicts the ratios  $E_L/E_0$  [Fig. 4(b)] and  $E_S/E_0$  [Fig. 4(c)] very well for both considered DG structures down to 10 micron wavelength below which it starts to deviate, nevertheless, remaining a reasonable estimate down to 3 microns. This is not surprising as the assumption of near-transparency is not valid as we go towards shorter wavelengths. For the 15 nm WG structure [long dashed lines in Fig. 4(c)] we find that the deviation from the long-wavelength limit is larger in comparison to the DG structures. Furthermore, we find that the DG structure with  $w_{x1} = 15$  nm outperforms the WG structure both in terms of achieved electric field enhancement and in terms of transmission. It is important to note, as we see in Fig. 3, that we have a two-dimensional (2D) confinement of the enhanced optical field for the DG structures, a useful feature for controlling light-matter interaction. This is not the case for the WG structures.

It is of particular interest to evaluate how much power is carried through the small gap region via the highly confined enhanced electric field. To illustrate this let us consider the spatial distribution of the z-component of the Poynting vector (time-average value),  $S_z$  for the DG structure of  $w_{x1} = 15$  nm, where we have an electric field enhancement factor of about 20 and confinement of the order of  $\sim (\lambda/250)^2$  in the small slit area at 10 microns [Fig. 5(a)]. As expected almost no power is transmitted through the metallic region while having a considerably larger power density in the small slit region compared to the large slit region.

We calculate the integrated  $S_z$  in the small slit region,  $P_s$ , and the large slit region,  $P_l$  for the DG structure of Fig. 5(a) within the unit cell. The respective areas of integration are designated in the figure. In Fig. 5(b) we show the fraction of power that goes through the small slits,  $F_{P_s} = P_s/(P_s + P_l)$ , as a function of free space wavelength for such structure. We observe a large  $F_{P_s}$  of about 30% that remains nearly constant for the entire spectral region of interest [Fig. 5(b)]. This is remarkable considering that the small slit region constitutes an area 60 times smaller than the unit cell area. At ~ 3 microns wavelength, the structural periodicity effects start to emerge and we observe a sharp increase in  $F_{P_s}$  with the total transmission having decreased sharply.

To quantify this behavior we find it useful to introduce a figure-of-merit namely, the "Power Confinement Factor" (PCF). We define PCF as the fraction of the incident power that gets funneled through the small slit region divided by the area fraction covered by the small slit region, i.e.  $PCF = TF_{P_s}a^2/A_s$ , with  $A_s$  being the area covered by the small grooves within the unit cell. It is analogous to the transmission enhancement factor in resonant EOT platforms. To illustrate this we compare the PCF for the DG structure of Fig. 3(a) to the WG structure of Fig. 3(c) for the same unit cell dimension for consistency although the WG does not really offer a 2D confinement. The PCF for both structures are nearly equal (~ 18) at 20 microns wavelength but decrease at different rates as we approach towards shorter wavelengths, with the PCF for the WG dropping much faster than the one for the DG structure. For example, near 3 microns wavelength the PCF for the DG structure is 13.5 while for the WG it is about 7.3, nearly half the value.

For this wavelength regime we observe an almost uniform magnetic field<sup>25</sup>. This enables estimation of the  $F_{P_s}$  ratio equaling  $1 - w_y/a$  using the quasistatic-limit values for the electric fields [eqs. (1) and (2)]. Hence, the PCF factor is equal to the field enhancement in the smallslit area [eq. 2(b)] implying that both can be simultaneoully optimized. For the parameters of the structure of Fig. 5(a), we obtain  $F_{P_s} \sim 33\%$ , which is very close to the calculated value of ~ 30%, that we described earlier. When we move away from the long-wavelength limit, the total transmission is better for the structures with the larger air area. The presence of the large aperture enables a more efficient funneling of the enhanced fields through the small aperture. This altogether implies the following:  $w_{x2}w_y + w_{x1}(a - w_y)$  controls the total transmission (the higher the greater),  $w_{x1}$  controls the enhancement factor of the fields within the slit and PCF factor (the smaller the greater),  $w_y/a$  controls the power ratio that goes through the small slits where the field is dramatically enhanced (the smaller the greater), and  $w_{x1}(a - w_y)$  controls the 2D confinement (the smaller the better; not applicable for WG). In other words, our proposed platform offers three different independent structural parameters:  $w_{x2}$ ,  $w_{x1}$  and  $w_y$ . By appropriately tuning these parameters one can control the localization and electric field enhancement, power confinement as well as electromagnetic energy transmission through the structure as necessary across a broad wavelength regime, pertinent to application specific demands.

In conclusion, our results constitute the first counterexample to the widespread and intuitive notion that resonances are needed to funnel light with enhanced intensity through deep subwavelength apertures. We achieve this by employing a simple double-groove structure that effectively combines the broadband transmission property of a one-dimensional grating<sup>16</sup> with the field confinement and enhancement properties of subwavelength apertures. Our structure possesses the attractive features of EOT platforms<sup>4</sup>, while being non-resonant and broadband. The structure described is relatively simple to implement and with constantly improving nanofabrication techniques is within the realm of possibility in the near future. Higher degree of enhancement is also possible, limited by a lower bound for the small-slit width, imposed by fabrication constraints and the onset of quantum tunneling of charges through the small-slit gap<sup>26</sup>. The demonstrated capabilities of our proposed platform can be important for optofluidic devices<sup>27</sup>, enhancement of non-linear phenomena and improving absorption efficiency in mid-IR detectors<sup>15</sup>.

This work was performed, in part, at the Center for Integrated Nanotechnologies, a U.S. Department of Energy, Office of Basic Energy Sciences user facility. Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.

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- <sup>18</sup>  $\varepsilon(\omega) = 1.0 \omega_p^2/(\omega(\omega + i\Gamma))$ , with  $\omega_p = 11.78 \cdot 10^{15}$  rad/sec, and  $\Gamma = 0.0895 \cdot 10^{15}$  rad/sec. Parameters are determined from an optimal fit to the available data in the region between 1 and 10 microns from E. Palik, *Handbook of Optical Constants of Solids*, Academic Press (1985).
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- $^{20}\,$  See supplemental material Fig. 1
- <sup>21</sup> This simulation is performed with Lumerical FDTD Solutions package; reference Guide for FDTD Solutions Release 7.0.1, http://www.lumerical.com/fdtd.
- <sup>22</sup> The corresponding field map for the structure of Fig. 3(a), but for 20nm within the substrate is shown in supplemental material Fig. 3(a).
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- <sup>24</sup> The corresponding Poynting vector map, but for 20nm within the substrate is shown in supplemental material Fig. 3(b).
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FIG. 1: (Color online) The proposed paradigm structure. It consists of Au patterned film of thickness  $d_{Au}$  resting on a  $d_{sub}$  thick substrate. The unit cell of the underlying square-lattice is magnified and depicted on the right panel (top view), with the associated geometric features designated.



FIG. 2: (Color online) Transmission (T), versus free space wavelength in microns. Five variations of the structure depicted in Fig. 1 are considered, all having  $d_{Au} = 50$  nm,  $d_{sub} = 500$  nm, and  $w_y = 200$  nm. ( $w_{x1}$  and  $w_{x2}$  for each case are given in the text. The adjacent icons depict the corresponding unit cell features to scale).



FIG. 3: (Color online) Spatial field distribution of the eletric field amplitude, normalized to an input field of 1V/m, at the middle of the Au film<sup>22</sup> for the structures with (a)  $w_{x1} = 15$  nm,  $w_{x2} = 100$  nm (b)  $w_{x1} = 50$  nm,  $w_{x2} = 100$  nm (c)  $w_{x1} = w_{x2} = 15$  nm and (d)  $w_{x1} = w_{x2} = 100$  nm. Remaining structural parameters are as in Fig. 2



FIG. 4: (Color online) Plotted versus free space wavelength (a) Ratio of the electric field amplitudes in the small and large slits (b) Normalized electric field amplitude in the large slit w.r.t source amplitude (c) Normalized electric field amplitude in the small slit w.r.t source amplitude. The dark (light) solid lines represent the result for the double-groove structure of Fig. 3(a) [Fig. 3(b)]. For comparison, the result for the 15 nm WG is shown in (c) with a long-dashed line. The dashed (dotted) lines represent the expected result from a quasi-static analysis in the long-wavelength limit for the DG structures of Fig. 3(a) [Fig. 3(b)]. The schematic on the right depicts a simple quasi-static picture of the charge response. The monitoring points are taken at the middle of the Au film. Their locations with respect to the structural unit cell, for the E<sub>S</sub> and E<sub>L</sub> fields, are also indicated.



FIG. 5: (Color online) (a) Spatial map of the Poynting vector, at the middle of the Au film<sup>24</sup>, for 10 microns incident wavelength for DG structure of Fig. 3 (a) (normalized to the incident Poynting vector) . (b) Corresponding ratio of the total power funneled through the small gap region,  $F_{P_s}$ , versus free space wavelength (c) Comparison of power confinement factor(PCF) versus free space wavelength for the DG structure (solid) of (a) with the 15nm WG result (dashed).